

Substitute for form 1449A/PTO				Complete if Known		
INEO	DMATION I	חופר	CHIPF	Application Number	10/685,380	
INFORMATION DISCLOSURE				Filing Date	October 16, 2003	
STATEMENT BY APPLICANT (use as many sheets as necessary)				First Named Inventor	Shinji MAEKAWA	
			ary)	Art Unit	2818	
				Examiner Name	David Goodwin	
Sheet	1	of	ı	Attorney Docket Number	740756-2660	

			U.S. PATENT DOCUME	INTS	
Examiner nitials	Cite No. 1	U.S. Patent Document Number - Kind Code ¹ (if known)	Publication Date MM-DD-YYŸY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	<u> </u>	OTHER PRIOR	ART – NON PATENT I	LITERATURE DOCUMENTS	<u></u>	
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.				T²
16		Kazuhiro SHIMIZU et al., "High-Mobility Poly-Si Thin-Film Transistors Fabricated by a Novel Excimer Laser Crystallization Method", IEEE TRANSACTIONS ON ELECTRON DEVICES., Vol. 40, No. 1, 1993, pp. 112-117.				

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Examiner Signature	DIMEN COOLIVEN	Date Considered	126/88

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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